

METHODS OF FORMING INTEGRATED CIRCUITS USING MASKS TO
PROVIDE ION IMPLANTATION SHIELDING TO PORTIONS OF A
SUBSTRATE ADJACENT TO AN ISOLATION REGION THEREIN AND
INTEGRATED CIRCUITS FORMED USING SAME

ABSTRACT

Methods of forming a channel region between isolation regions of an
5 integrated circuit substrate are disclosed. In particular, a mask can be formed on an
isolation region that extends onto a portion of the substrate adjacent to the isolation
region to provide a shielded portion of the substrate adjacent to the isolation region
and an exposed portion of the substrate spaced apart from the isolation region having
the shielded portion therebetween. A channel region can be formed in the exposed
10 portion of the substrate. Related integrated circuits are also discussed.